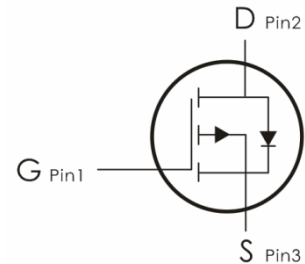
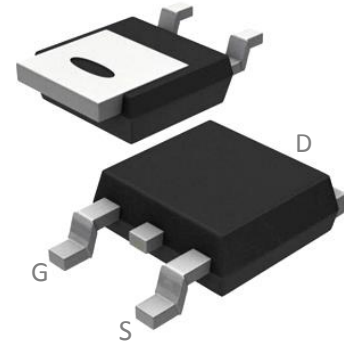


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-60V, I_D=-15A, R_{DS(ON)}<0.090\ \Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Continuous Drain Current	-15	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	-9.5	
	Pulsed Drain Current ¹	-45	
P_D	Power Dissipation	36	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	110	

Package Marking and Ordering Information:

Part NO.	Marking	Package
IRFR9024N	IRFR9024N	TO-252

Electrical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu A$	-60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-60V$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu A$	-1	---	-3	V
$R_{DS(ON)}$	Drain-Source On Resistance ²	$V_{GS}=-10V, I_D=-12A$	---	---	90	m Ω
		$V_{GS}=-4.5V, I_D=-9A$	---	---	120	
G_{FS}	Forward Transconductance	$V_{DS}=-10V, I_D=-9A$	---	14	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$	---	1660	2660	pF
C_{oss}	Output Capacitance		---	160	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time ²	$V_{DS}=-30V, I_D=-9A,$ $R_{GEN}=3.3\ \Omega, V_{GS}=-10V$	---	10	---	ns
t_r	Rise Time		---	19	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	46	---	ns
t_f	Fall Time		---	53	---	ns
Q_g	Total Gate Charge ²		---	17	27	nC
Q_{gs}	Gate-Source Charge	$V_{GS}=-4.5V, V_{DS}=-48V,$ $I_D=-9A$	---	5	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	6	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ²	$V_{GS}=0V, I_S=-9A, T_J=25^\circ\text{C}$	---	---	-1.2	V
T_{rr}	Reverse Recovery Time ²	$I_S=-9A, V_{GS}=0V.$ $di/dt=100A/us$	---	56	---	Ns
Q_{rr}	Reverse Recovery Charge		---	159	---	nc

Notes: 1.Pulse width limited by Max. junction temperature.

 2.Pulse width $\leq 300us$, dutycycle $\leq 2\%$.

Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

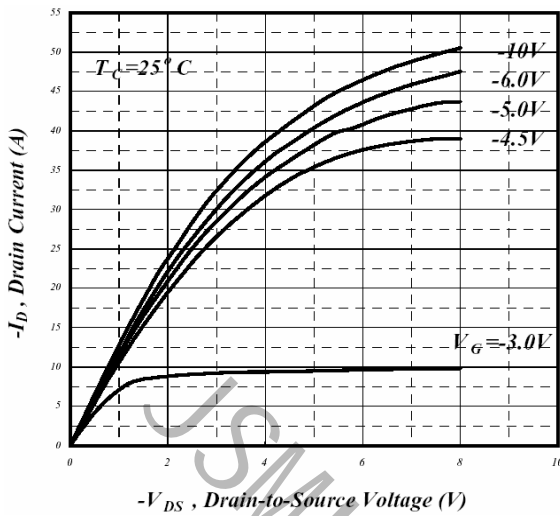


Fig 1. Typical Output Characteristics

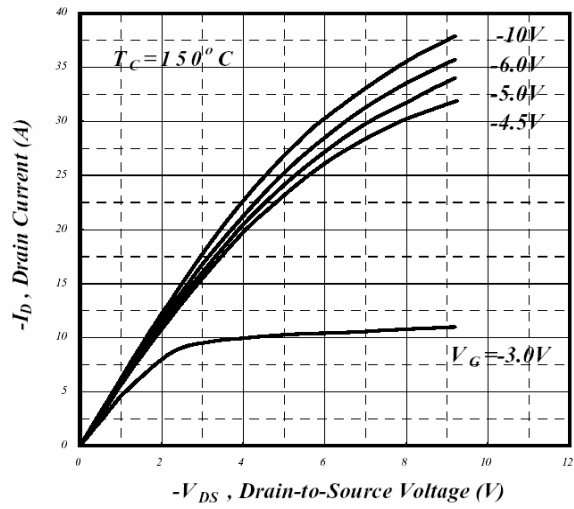


Fig 2. Typical Output Characteristics

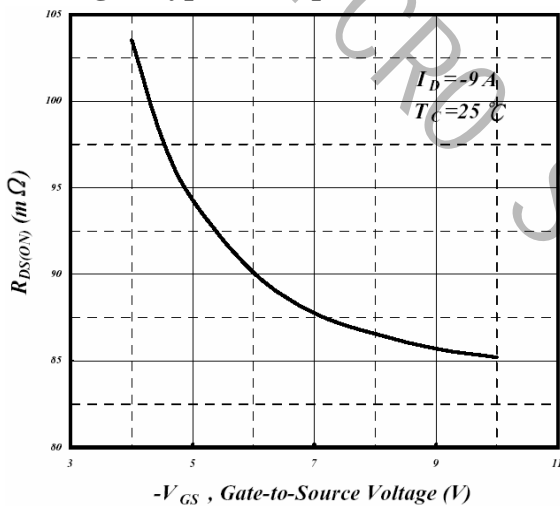


Fig 3. On-Resistance v.s. Gate Voltage

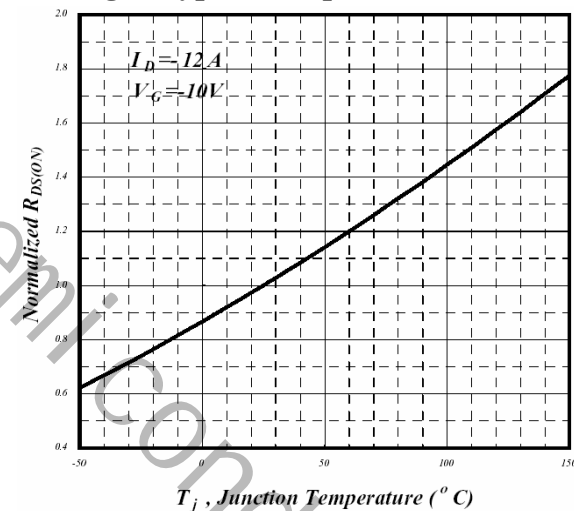


Fig 4. Normalized On-Resistance v.s. Junction Temperature

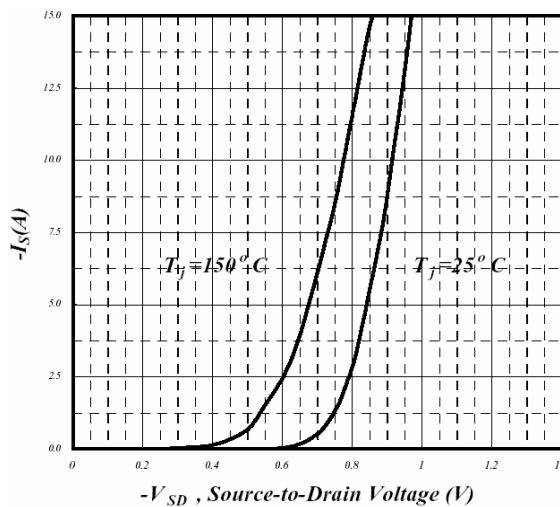


Fig 5. Forward Characteristics of Reverse Diode

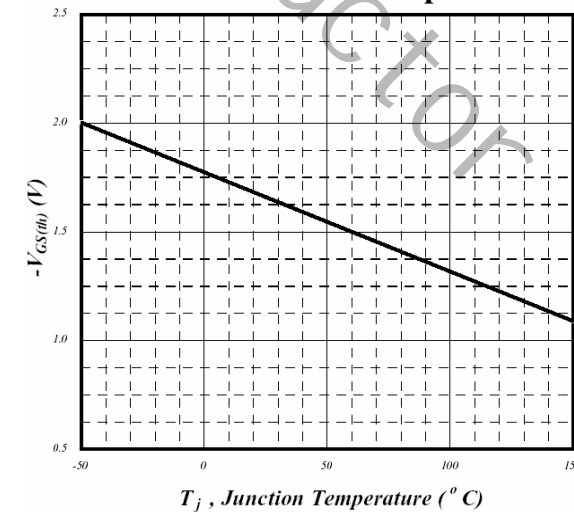


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

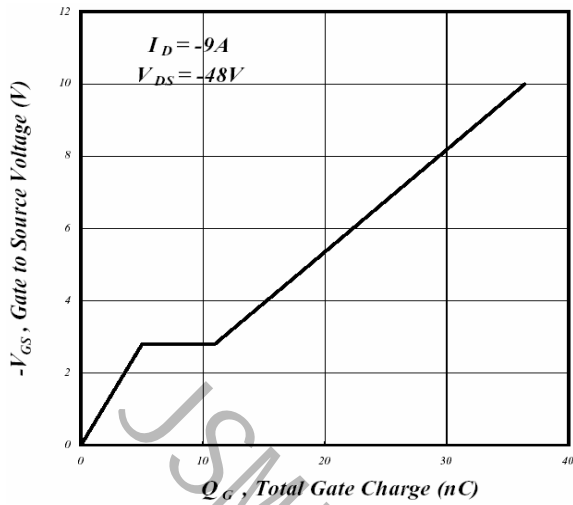


Fig 7. Gate Charge Characteristics

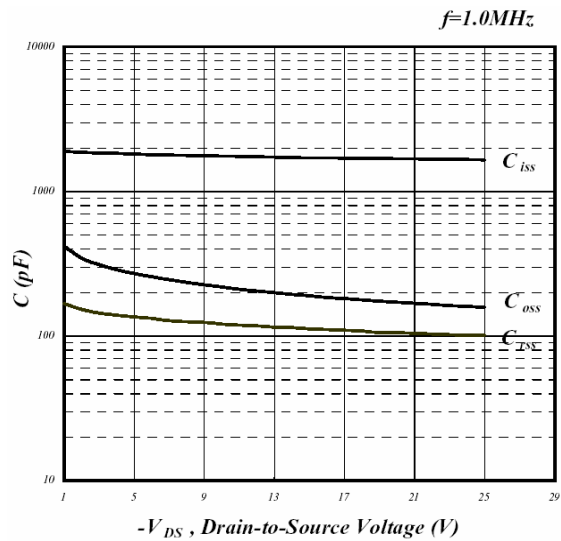


Fig 8. Typical Capacitance Characteristics

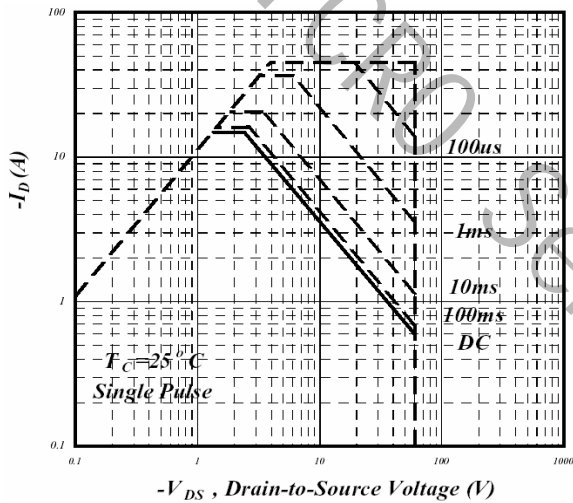


Fig 9. Maximum Safe Operating Area

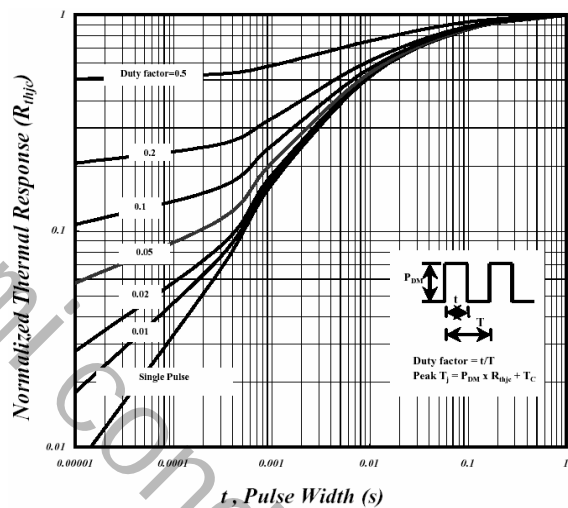


Fig 10. Effective Transient Thermal Impedance

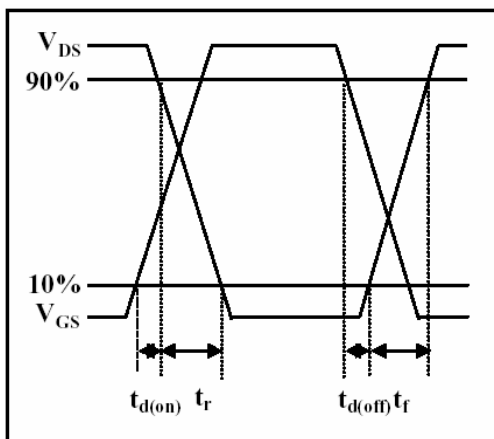


Fig 11. Switching Time Waveform

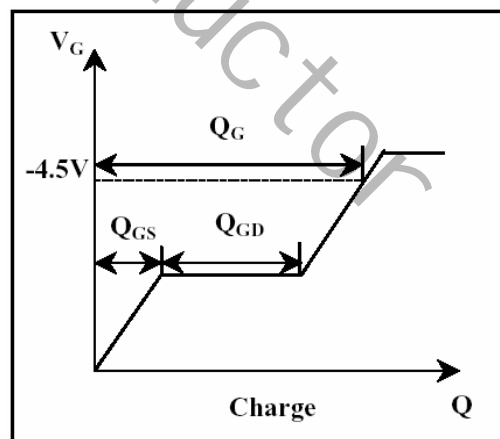


Fig 12. Gate Charge Waveform